Åemsettin Altindal

List of Publications by Year
in descending order

143 papers	3,963 citations	125106 35 h-index	206121 51 g-index
144 all docs	144 docs citations	144 times ranked	1681 citing authors

#	Article	IF	Citations
1	Dielectric properties, electric modulus and conductivity profiles of Al/Al2O3/p-Si type MOS capacitor in large frequency and bias interval. Engineering Science and Technology, an International Journal, 2022, 27, 101017.	2.0	10
2	Dielectric Properties of PVP: BaTiO3 Interlayer in the Al/PVP: BaTiO3/P-Si Structure. Silicon, 2022, 14, 5437-5443.	1.8	12
3	High Dielectric Performance of Heterojunction Structures Based on Spin-Coated Graphene-PVP Thin Film on Silicon With Gold Contacts for Organic Electronics. IEEE Transactions on Electron Devices, 2022, 69, 304-310.	1.6	10
4	Identification of Current Transport Mechanisms and Temperature Sensing Qualifications for Al/(ZnS-PVA)/p-Si Structures at Low and Moderate Temperatures. IEEE Sensors Journal, 2022, 22, 99-106.	2.4	18
5	A comparison of Au/n-Si Schottky diodes (SDs) with/without a nanographite (NG) interfacial layer by considering interlayer, surface states (N_{ss}) and series resistance (R_s) effects. Physica Scripta, 2022, 97, 055811.	1.2	17
6	The illumination effects on the current conduction mechanisms of the Au/(<scp>Er₂O₃</scp>:<scp>PVC</scp>)/<scp>nâ€Si</scp> (<scp>MPS</scp>) Schottky diodes. Journal of Applied Polymer Science, 2022, 139, .	1.3	19
7	Discrepancies in barrier heights obtained from currentâ€“voltage (IV) and capacitanceâ€“voltage (CV) of Au/PNoMPhPPy/n-GaAs structures in wide range of temperature. Journal of Materials Science: Materials in Electronics, 2022, 33, 12210-12223.	1.1	17
8	Dielectric properties and negative-capacitance/dielectric in Au/n-Si structures with PVC and (PVC:Sm2O3) interlayer. Materials Science in Semiconductor Processing, 2022, 147, 106754.	1.9	13
9	The effect of cadmium impurities in the (PVPâ€“TeO2) interlayer in Al/p-Si (MS) Schottky barrier diodes (SBDs): Exploring its electrophysical parameters. Physica B: Condensed Matter, 2021, 604, 412617.	1.3	18
10	Current transport properties of (Au/Ni)/HfAlO3/n-Si metalâ€“insulatorâ€“semiconductor junction. Journal of Physics and Chemistry of Solids, 2021, 148, 109758.	1.9	23
11	Frequency Response of Câ€“V and G/Ï‰-V Characteristics of Au/(Nanographite-doped PVP)/n-Si Structures. Journal of Materials Science: Materials in Electronics, 2021, 32, 993-1006.	1.1	20
12	Investigation of the variation of dielectric properties by applying frequency and voltage to Al/(CdS-PVA)/p-Si structures. Journal of Molecular Structure, 2021, 1224, 129325.	1.8	24
13	Electrical characterizationÂof Au/n-Si (MS) diode with and without graphene-polyvinylpyrrolidone (Gr-PVP) interface layer. Journal of Materials Science: Materials in Electronics, 2021, 32, 3451-3459.	1.1	19
14	Frequency dependence of the dielectric properties of Au/(NG:PVP)/n-Si structures. Journal of Materials Science: Materials in Electronics, 2021, 32, 7657-7670.	1.1	25
15	Evaluation of gamma-irradiation effects on the electrical properties of Al/(ZnO-PVA)/p-Si type Schottky diodes using current-voltage measurements. Radiation Physics and Chemistry, 2021, 183, 109430.	1.4	29
16	Illumination and voltage effects on the forward and reverse bias currentâ€“voltage (I-V) characteristics in In/In2S3/p-Si photodiodes. Journal of Materials Science: Materials in Electronics, 2021, 32, 21825-21836.	1.1	21
17	Effect of (Coâ€“TeO2-doped polyvinylpyrrolidone) organic interlayer on the electrophysical characteristics of Al/p-Si (MS) structures. Journal of Materials Science: Materials in Electronics, 2021, 32, 21909-21922.	1.1	16
18	A comparison of electrical characteristics of Au/n-Si (MS) structures with PVC and (PVC:) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50.62 Td (Sr	1.2	35

#	ARTICLE	IF	CITATIONS
19	Graphene doped (Bi2Te3â€“Bi2O3â€“TeO2): PVP dielectrics in metalâ€“semiconductor structures. Applied Physics A: Materials Science and Processing, 2021, 127, 1.	1.1	11
20	Comparison of dielectric characteristics for metalâ€“semiconductor structures fabricated with different interlayers thicknesses. Journal of Materials Science: Materials in Electronics, 2021, 32, 26700-26708.	1.1	3
21	Frequency Response of Metalâ€“Semiconductor Structures With Thin-Films Sapphire Interlayer by ALD Technique. IEEE Transactions on Electron Devices, 2021, 68, 5085-5089.	1.6	11
22	Comparison of the electrical and impedance properties of Au/(ZnOMn:PVP)/n-Si (MPS) type Schottky-diodes (SDs) before and after gamma-irradiation. Physica Scripta, 2021, 96, 125881.	1.2	20
23	Comparison of electrical properties of MS and MPS type diode in respect of (In2O3-PVP) interlayer. Physica B: Condensed Matter, 2020, 576, 411733.	1.3	46
24	Frequency and voltage dependence of barrier height, surface states, and series resistance in Al/Al2O3/p-Si structures in wide range frequency and voltage. Physica B: Condensed Matter, 2020, 582, 411979.	1.3	51
25	Effect of illumination on electrical parameters of Au/(P3DMTFT)/n-GaAs Schottky barrier diodes. Indian Journal of Physics, 2020, 94, 1901-1908.	0.9	25
26	Identifying of series resistance and interface states on rhenium/n-GaAs structures using Câ€“Vâ€“T and G/Ï‰â€“Vâ€“T characteristics in frequency ranged 50ÂkHz to 5ÂMHz. Journal of Materials Science: Materials in Electronics, 2020, 31, 704-713.	1.1	5
27	The effects of (Bi2Te3â€“Bi2O3-TeO2-PVP) interfacial film on the dielectric and electrical features of Al/p-Si (MS) Schottky barrier diodes (SBDs). Physica B: Condensed Matter, 2020, 582, 411958.	1.3	33
28	Electrical and dielectric properties of Al/(PVP: Zn-TeO2)/p-Si heterojunction structures using currentâ€“voltage (Iâ€“V) and impedance-frequency (Zâ€“f) measurements. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	1.1	33
29	Electrical characteristics of Au/PVP/n-Si structures using admittance measurements between 1 and 500ÂkHz. Journal of Materials Science: Materials in Electronics, 2020, 31, 13337-13343.	1.1	7
30	Electric and dielectric parameters in Au/n-Si (MS) capacitors with metal oxide-polymer interlayer as function of frequency and voltage. Journal of Materials Science: Materials in Electronics, 2020, 31, 15589-15598.	1.1	26
31	Investigation of effects on dielectric properties of different doping concentrations of Au/Gr-PVA/p-Si structures at 0.1 and 1ÂMHz at room temperature. Journal of Materials Science: Materials in Electronics, 2020, 31, 16324-16331.	1.1	3
32	A comparison study regarding Al/p-Si and Al/(carbon nanofiberâ€“PVP)/p-Si diodes: current/impedanceâ€“voltage (I/Zâ€“V) characteristics. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	1.1	13
33	A Highly Sensitive Temperature Sensor Based on Au/Graphene-PVP/<i>n</i>-Si Type Schottky Diodes and the Possible Conduction Mechanisms in the Wide Range Temperatures. IEEE Sensors Journal, 2020, 20, 14081-14089.	2.4	37
34	A comparative study on the electrical properties and conduction mechanisms of Au/n-Si Schottky diodes with/without an organic interlayer. Journal of Materials Science: Materials in Electronics, 2020, 31, 14466-14477.	1.1	32
35	The possible current-conduction mechanism in the Au/(CoSO4-PVP)/n-Si junctions. Journal of Materials Science: Materials in Electronics, 2020, 31, 18640-18648.	1.1	11
36	On the electrical characteristics of Al/p-Si diodes with and without (PVP: Sn-TeO2) interlayer using currentâ€“voltage (Iâ€“V) measurements. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	1.1	14

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37	Frequency and voltage dependence of electrical and dielectric properties in metal-interfacial layer-semiconductor (MIS) type structures. Physica B: Condensed Matter, 2020, 587, 412122.	1.3	36
38	Intersection behavior of the currentâ€“voltage (Iâ€“V) characteristics of the (Au/Ni)/HfAlO3/n-Si (MIS) structure depends on the lighting intensity. Journal of Materials Science: Materials in Electronics, 2020, 31, 13167-13172.	1.1	9
39	On the frequency and voltage-dependent main electrical parameters of the Au/ZnO/n-GaAs structures at room temperature by using various methods. Physica B: Condensed Matter, 2020, 594, 412274.	1.3	23
40	The origin of anomalous peak and negative capacitance on dielectric behavior in the accumulation region in Au/(0.07 Zn-doped polyvinyl alcohol)/n-4Hâ€“SiC metal-polymer-semiconductor structures/diodes studied by temperature-dependent impedance measurements. Journal of Physics and Chemistry of Solids, 2020, 144, 109523.	1.9	26
41	Investigation of the effect of different Bi2O3â€“x:PVA (xâ€‰=â€‰Sm, Sn, Mo) thin insulator interface-layer materials on diode parameters. Journal of Materials Science: Materials in Electronics, 2020, 31, 8033-8042.	1.1	9
42	Frequency-Dependent Admittance Analysis of Au/n-Si Structure with CoSO4-PVP Interfacial Layer. Journal of Electronic Materials, 2020, 49, 3720-3727.	1.0	26
43	Investigation of gamma-irradiation effects on electrical characteristics of Al/(ZnOâ€“PVA)/p-Si Schottky diodes using capacitance and conductance measurements. Journal of Materials Science: Materials in Electronics, 2020, 31, 8349-8358.	1.1	14
44	The interfacial properties of Au/n-4H-SiC structure with (Zn-doped PVA) interfacial layer. Physica Scripta, 2020, 95, 115809.	1.2	4
45	Investigation of Dielectric Properties, Electric Modulus and Conductivity of the Au/Zn-Doped PVA/<i>n</i>-4H-SiC (MPS) Structure Using Impedance Spectroscopy Method. Zeitschrift Fur Physikalische Chemie, 2020, 234, 505-516.	1.4	5
46	Dielectric properties of $$hbox {Ag/Ru}_{0.03}$$â€“PVA/n-Si structures. Bulletin of Materials Science, 2019, 42, 1.	0.8	4
47	Dielectric characterization of BSA doped-PANI interlayered metalâ€“semiconductor structures. Journal of Materials Science: Materials in Electronics, 2019, 30, 14224-14232.	1.1	15
48	Determination of current transport and trap states density in AlInGaN/GaN heterostructures. Microelectronics Reliability, 2019, 103, 113517.	0.9	15
49	Investigation of the efficiencies of the (SnO2-PVA) interlayer in Au/n-Si (MS) SDs on electrical characteristics at room temperature by comparison. Journal of Materials Science: Materials in Electronics, 2019, 30, 20479-20488.	1.1	23
50	Examination of dielectric response of Au/HgS-PVA/n-Si (MPS) structure by impedance spectroscopy method. Physica B: Condensed Matter, 2019, 566, 125-135.	1.3	39
51	Synthesis of boron and rare earth stabilized graphene doped polyvinylidene fluoride (PVDF) nanocomposite piezoelectric materials. Polymer Composites, 2019, 40, 3623-3633.	2.3	27
52	On the possible conduction mechanisms in Rhenium/n-GaAs Schottky barrier diodes fabricated by pulsed laser deposition in temperature range of 60â€“400ÂK. Journal of Materials Science: Materials in Electronics, 2019, 30, 9029-9037.	1.1	21
53	A comparison of electrical parameters of Au/n-Si and Au/(CoSO4â€“PVP)/n-Si structures (SBDs) to determine the effect of (CoSO4â€“PVP) organic interlayer at room temperature. Journal of Materials Science: Materials in Electronics, 2019, 30, 9273-9280.	1.1	36
54	The fabrication of Al/p-Si (MS) type photodiode with (%2 ZnO-doped CuO) interfacial layer by sol gel method and their electrical characteristics. Physica B: Condensed Matter, 2019, 560, 91-96.	1.3	39

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55	A comparative study on current/capacitance: voltage characteristics of Au/n-Si (MS) structures with and without PVP interlayer. Journal of Materials Science: Materials in Electronics, 2019, 30, 6491-6499.	1.1	32
56	Determination of Surface States Energy Density Distributions and Relaxation Times for a Metal-Polymer-Semiconductor Structure. IEEE Nanotechnology Magazine, 2019, 18, 1196-1199.	1.1	21
57	Thermal Annealing Effects on the Electrical and Structural Properties of Ni/Pt Schottky Contacts on the Quaternary AlInGaN Epilayer. Journal of Electronic Materials, 2019, 48, 887-897.	1.0	8
58	Frequency-Dependent Admittance Analysis of the Metalâ€“Semiconductor Structure With an Interlayer of Zn-Doped Organic Polymer Nanocomposites. IEEE Transactions on Electron Devices, 2018, 65, 231-236.	1.6	38
59	Effects of a Thin Ru-Doped PVP Interface Layer on Electrical Behavior of Ag/n-Si Structures. Journal of Electronic Materials, 2018, 47, 3510-3520.	1.0	25
60	Preparation and characterization of cross-linked poly (vinyl alcohol)-graphene oxide nanocomposites as an interlayer for Schottky barrier diodes. International Journal of Modern Physics B, 2018, 32, 1750276.	1.0	8
61	Role of Graphene-Doped Organic/Polymer Nanocomposites on the Electronic Properties of Schottky Junction Structures for Photocell Applications. Journal of Electronic Materials, 2018, 47, 7134-7142.	1.0	17
62	Evaluation of Electric and Dielectric Properties of Metalâ€“Semiconductor Structures With 2% GC-Doped-(Ca₃Co₄Ga_{0.001}O_{<i>x</i>}) Interlayer. IEEE Transactions on Electron Devices, 2018, 65, 3901-3908.	1.6	30
63	A comparative study on dielectric behaviours of Au/(Zn-doped PVA)/n-4H-SiC (MPS) structures with different interlayer thicknesses using impedance spectroscopy methods. Bulletin of Materials Science, 2018, 41, 1.	0.8	13
64	Preparation of (CuSâ€“PVA) interlayer and the investigation their structural, morphological and optical properties and frequency dependent electrical characteristics of Au/(CuSâ€“PVA)/n-Si (MPS) structures. Journal of Materials Science: Materials in Electronics, 2018, 29, 11801-11811.	1.1	19
65	Dielectric properties, electrical modulus and current transport mechanisms of Au/ZnO/n-Si structures. Progress in Natural Science: Materials International, 2018, 28, 325-331.	1.8	53
66	Effectuality of Barrier Height Inhomogeneity on the Currentâ€“Voltageâ€“Temperature Characteristics of Metal Semiconductor Structures with CdZnO Interlayer. Journal of Electronic Materials, 2018, 47, 6059-6066.	1.0	46
67	Temperature and Interfacial Layer Effects on the Electrical and Dielectric Properties of Al/(CdS-PVA)/p-Si (MPS) Structures. Journal of Electronic Materials, 2018, 47, 6600-6606.	1.0	13
68	Preparation of mixed copper/PVA nanocomposites as an interface layer for fabrication of Al/Cu-PVA/p-Si Schottky structures. Physica B: Condensed Matter, 2018, 546, 93-98.	1.3	34
69	Determining electrical and dielectric parameters of Al/ZnS-PVA/p-Si (MPS) structures in wide range of temperature and voltage. Journal of Materials Science: Materials in Electronics, 2018, 29, 12735-12743.	1.1	11
70	Controlling the electrical characteristics of Au/nâ€Si structure with and without (biphenylâ€CoPc) and (OHSubsâ€ZnPc) interfacial layers at room temperature. Polymers for Advanced Technologies, 2017, 28, 952-957.	1.6	6
71	Investigation of photo-induced effect on electrical properties of Au/PPy/n-Si (MPS) type schottky barrier diodes. Journal of Materials Science: Materials in Electronics, 2017, 28, 6413-6420.	1.1	16
72	Investigation of frequency and voltage dependence surface states and series resistance profiles using admittance measurements in Al/p-Si with Co 3 O 4 -PVA interlayer structures. Physica B: Condensed Matter, 2017, 515, 28-33.	1.3	43

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73	Two-diode behavior in metal-ferroelectric-semiconductor structures with bismuth titanate interfacial layer. International Journal of Modern Physics B, 2017, 31, 1750197.	1.0	3
74	Electric and Dielectric Properties of Au/ZnS-PVA/n-Si (MPS) Structures in the Frequency Range of 10â€“200Â kHz. Journal of Electronic Materials, 2017, 46, 4276-4286.	1.0	34
75	Investigation of the C-V characteristics that provides linearity in a large reverse bias region and the effects of series resistance, surface states and interlayer in Au/n-Si/Ag diodes. Journal of Alloys and Compounds, 2017, 708, 464-469.	2.8	22
76	On the Frequency and Voltage-Dependent Profiles of the Surface States and Series Resistance of Au/ZnO/n-Si Structures in a Wide Range of Frequency and Voltage. Journal of Electronic Materials, 2017, 46, 5728-5736.	1.0	34
77	Determining electrical and dielectric parameters of dependence as function of frequencies in Al/ZnS-PVA/p-Si (MPS) structures. Journal of Materials Science: Materials in Electronics, 2017, 28, 1315-1321.	1.1	38
78	Interfacial layer thickness dependent electrical characteristics of Au/(Zn-doped PVA)/<i>n</i>-4H-SiC (MPS) structures at room temperature. EPJ Applied Physics, 2017, 80, 10101.	0.3	19
79	Frequency and voltage dependence dielectric properties, ac electrical conductivity and electric modulus profiles in Al/Co 3 O 4 -PVA/p-Si structures. Physica B: Condensed Matter, 2016, 500, 154-160.	1.3	54
80	Double exponential Iâ€“V characteristics and double Gaussian distribution of barrier heights in (Au/Ti)/Al2O3/n-GaAs (MIS)-type Schottky barrier diodes in wide temperature range. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	1.1	57
81	Investigation of Electrical Characteristics in Al/CdS-PVA/p-Si (MPS) Structures Using Impedance Spectroscopy Method. IEEE Transactions on Electron Devices, 2016, 63, 2948-2955.	1.6	79
82	A Comparative Study on the Main Electrical Parameters of Au/<I>n</I>-Si, Au/Biphenyl-CuPc/<I>n</I>-Si/ and Au/Biphenylsubs-CoPc/<I>n</I>-Si/ Type Schottky Barrier Diodes. Journal of Nanoelectronics and Optoelectronics, 2016, 11, 620-625.	0.1	5
83	Investigation of dielectric relaxation and ac electrical conductivity using impedance spectroscopy method in (AuZn)/TiO2/p-GaAs(110) schottky barrier diodes. Journal of Alloys and Compounds, 2015, 628, 442-449.	2.8	90
84	The source of negative capacitance and anomalous peak in the forward bias capacitance-voltage in Cr/p-si Schottky barrier diodes (SBDs). Materials Science in Semiconductor Processing, 2015, 39, 484-491.	1.9	74
85	Dielectric properties and electric modulus of Au/PPy/n-Si (MPS) type Schottky barrier diodes (SBDS) as a function of frequency and applied bias voltage. International Journal of Modern Physics B, 2015, 29, 1550075.	1.0	18
86	Dielectric spectroscopy studies and ac electrical conductivity on (AuZn)/TiO₂/p-GaAs(110) MIS structures. Philosophical Magazine, 2015, 95, 2885-2898.	0.7	33
87	Comparative study of the temperature-dependent dielectric properties of Au/PPy/n-Si (MPS)-type Schottky barrier diodes. Journal of the Korean Physical Society, 2015, 67, 889-895.	0.3	16
88	Electrical characteristics of Au/PVA (x-doped)/n-Si: Comparison study on the effect of dopant type in PVA. Fibers and Polymers, 2014, 15, 2253-2259.	1.1	2
89	Frequency and voltage-dependent electrical and dielectric properties of Al/Co-doped PVA/p-Si structures at room temperature. Chinese Physics B, 2014, 23, 047304.	0.7	37
90	Single Gaussian distribution of barrier height in Al/PSâ€“ZnPc/p-Si type Schottky barrier diode in temperature range of 120â€“320Â K. Journal of Materials Science: Materials in Electronics, 2014, 25, 4391-4397.	1.1	11

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91	Electrical and dielectric properties and intersection behavior of G/Ï‰-V plots for Al/Co-PVA/p-Si (MPS) structures at temperatures below room temperature. Journal of the Korean Physical Society, 2014, 65, 2082-2089.	0.3	20
92	Capacitance/Conductanceâ€“Voltageâ€“Frequency Characteristics of ${m Au}/{m PVC}+{m TCNQ}/{m p}hbox{-}{m Si}$ Structures in Wide Frequency Range. IEEE Transactions on Electron Devices, 2014, 61, 584-590.	1.6	28
93	Charge transport mechanisms and density of interface traps in MnZnO/p-Si diodes. Journal of Alloys and Compounds, 2014, 590, 157-161.	2.8	69
94	Dielectric and Optical Properties of CdSâ€“Polymer Nanocomposites Prepared by the Successive Ionic Layer Adsorption and Reaction (SILAR) Method. Journal of Electronic Materials, 2014, 43, 1226-1231.	1.0	18
95	Investigation of currentâ€voltage characteristics and current conduction mechanisms in composites of polyvinyl alcohol and bismuth oxide. Polymer Engineering and Science, 2014, 54, 1811-1816.	1.5	8
96	Frequency and Voltage Dependence of Dielectric Loss of MgB2 Composites at Different Temperatures. Journal of Superconductivity and Novel Magnetism, 2013, 26, 2165-2170.	0.8	0
97	A study of polymer-derived erbia-doped Bi2O3 nanocrystalline ceramic powders. Journal of Sol-Gel Science and Technology, 2013, 66, 317-323.	1.1	1
98	The origin of negative capacitance in Au/n-GaAs Schottky barrier diodes (SBDs) prepared by photolithography technique in the wide frequency range. Current Applied Physics, 2013, 13, 1101-1108.	1.1	34
99	The effect of metal work function on the barrier height of metal/CdS/SnO2/Inâ€“Ga structures. Current Applied Physics, 2013, 13, 1306-1310.	1.1	15
100	A detailed comparative study on the main electrical parameters of Au/n-Si and Au/PVA:Zn/n-Si Schottky barrier diodes. Materials Science in Semiconductor Processing, 2013, 16, 1865-1872.	1.9	41
101	On the Voltage and Frequency Distribution of Dielectric Properties and ac Electrical Conductivity in Al/SiO ₂ /p-Si (MOS) Capacitors. Chinese Physics Letters, 2013, 30, 017301.	1.3	21
102	The Main Electrical and Interfacial Properties of Benzotriazole and Fluorene Based Organic Devices. Journal of Macromolecular Science - Pure and Applied Chemistry, 2013, 50, 168-174.	1.2	13
103	Analyses of temperature-dependent interface states, series resistances, and AC electrical conductivities of Al/pâ€"Si and Al/Bi 4 Ti 3 O 12 /pâ€"Si structures by using the admittance spectroscopy method. Chinese Physics B, 2013, 22, 108502.	0.7	12
104	On the energy distribution of interface states and their relaxation time profiles in Al/pentacene/p-GaAs heterojunction diode. Journal of Applied Physics, 2012, 111, 034508.	1.1	15
105	Effects of interface states and series resistance on electrical properties of Al/nanostructure CdO/p-GaAs diode. Journal of Alloys and Compounds, 2012, 541, 462-467.	2.8	37
106	Temperature dependent negative capacitance behavior of Al/rhodamine-101/n-GaAs Schottky barrier diodes and Rs effects on the Câ€“V and G/Ï‰â€“V characteristics. Journal of Alloys and Compounds, 2012, 513, 107-111.	2.8	53
107	The effects of temperature, radiation, and illumination on currentâ€“voltage characteristics of Au/PVA(Co, Znâ€doped)/nâ€Si Schottky diodes. Journal of Applied Polymer Science, 2012, 125, 1185-1192.	1.3	18
108	The effect of gamma irradiation on electrical and dielectric properties of Al-TiW-Pd2Si/n-Si Schottky diode at room temperature. Current Applied Physics, 2012, 12, 860-864.	1.1	9

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109	The effect of gamma irradiation on electrical and dielectric properties of organic-based Schottky barrier diodes (SBDs) at room temperature. Radiation Physics and Chemistry, 2012, 81, 362-369.	1.4	25
110	Structural and electrical characterization of rectifying behavior in n-type/intrinsic ZnO-based homojunctions. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2012, 177, 588-593.	1.7	11
111	Illumination intensity effects on the dielectric properties of schottky devices with Co, Niâ€doped PVA nanofibers as an interfacial layer. Advances in Polymer Technology, 2012, 31, 63-70.	0.8	18
112	The forward bias current densityâ€"voltageâ€"temperature (<i>Jâ€"Vâ€"T</i>) characteristics of Alâ€"SiO₂â€"pSi (MIS) Schottky diodes. International Journal of Electronics, 2011, 98, 699-712.	0.9	3
113	The origin of anomalous peak and negative capacitance in the forward bias capacitance-voltage characteristics of Au/PVA/n-Si structures. Journal of Applied Physics, 2011, 109, .	1.1	87
114	On the mechanism of current-transport in Cu/CdS/SnO2/Inâ€"Ga structures. Journal of Alloys and Compounds, 2011, 509, 5555-5561.	2.8	45
115	Analysis of the forward and reverse bias <i>I-V</i> characteristics on Au/PVA:Zn/n-Si Schottky barrier diodes in the wide temperature range. Journal of Applied Physics, 2011, 109, .	1.1	48
116	Illumination Effect on Admittance Measurements of Polyvinyl Alcohol (Co, Zn-Doped)âˆ•n-Si Schottky Barrier Diodes in Wide Frequency and Applied Bias Voltage Range. , 2011, , .		1
117	Comparative Analysis of Temperature-Dependent Electrical and Dielectric Properties of an $hbox{Al}{-}hbox{TiW}{-}hbox{Pd}_{2}hbox{Si/n-Si}$ Schottky Device at Two Frequencies. IEEE Transactions on Electron Devices, 2011, 58, 4042-4048.	1.6	16
118	Electrical characterization of MS and MIS structures on AlGaN/AlN/GaN heterostructures. Microelectronics Reliability, 2011, 51, 370-375.	0.9	43
119	Preparation and dielectric properties of polyvinyl alcohol (Co, Zn Acetate) Fiber/n-Si and polyvinyl alcohol (Ni, Zn Acetate)/n-Si Schottky diodes. Fibers and Polymers, 2011, 12, 886-892.	1.1	11
120	Anomalous Peak in the Forward-Bias Câ€"V Plot and Temperature-Dependent Behavior of Au/PVA (Ni,Zn-doped)/n-Si(111) Structures. Journal of Electronic Materials, 2011, 40, 157-164.	1.0	61
121	The illumination intensity and applied bias voltage on dielectric properties of au/polyvinyl alcohol (Co, Znâ€doped)/nâ€Si Schottky barrier diodes. Journal of Applied Polymer Science, 2011, 120, 322-328.	1.3	37
122	Temperature dependent currentâ€"voltage (Iâ€"V) characteristics of Au/n-Si (111) Schottky barrier diodes with PVA(Ni,Zn-doped) interfacial layer. Materials Science in Semiconductor Processing, 2011, 14, 139-145.	1.9	57
123	The role of 60Co Î³-ray irradiation on the interface states and series resistance in MIS structures. Radiation Physics and Chemistry, 2010, 79, 457-461.	1.4	16
124	The effect of insulator layer thickness on the main electrical parameters in (Ni/Au)/AlxGa1âˆ'xN/AlN/GaN heterostructures. Surface and Interface Analysis, 2010, 42, 803-806.	0.8	3
125	Illumination effect on electrical characteristics of organic-based Schottky barrier diodes. Journal of Applied Physics, 2010, 108, .	1.1	27
126	Frequency and Temperature Dependence of Dielectric Properties of Au/Polyvinyl Alcohol (Co,) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 67 T Biomaterials, 2010, 59, 739-756.	1.8	25

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127	The explanation of barrier height inhomogeneities in Au/n-Si Schottky barrier diodes with organic thin interfacial layer. Journal of Applied Physics, 2010, 108, .	1.1	87
128	Temperature dependent negative capacitance behavior in (Ni/Au)/AlGaN/AlN/GaN heterostructures. Journal of Non-Crystalline Solids, 2010, 356, 1006-1011.	1.5	70
129	The distribution of barrier heights in MIS type Schottky diodes from currentâ€“voltageâ€“temperature (Iâ€“Vâ€“T) measurements. Journal of Alloys and Compounds, 2009, 479, 893-897.	2.8	67
130	Tunneling current via dislocations in Schottky diodes on AlInN/AlN/GaN heterostructures. Semiconductor Science and Technology, 2009, 24, 075003.	1.0	75
131	Dislocation-governed current-transport mechanism in (Ni/Au)â€“AlGaN/AlN/GaN heterostructures. Journal of Applied Physics, 2009, 105, .	1.1	89
132	Frequency and gate voltage effects on the dielectric properties of Au/SiO2/n-Si structures. Microelectronic Engineering, 2008, 85, 1910-1914.	1.1	55
133	Effects of Î³-ray irradiation on the Câ€“V and G/Ï‰â€“V characteristics of Al/SiO2/p-Si (MIS) structures. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 791-796.	0.6	15
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